



BUK9Y4R8-60RA

N-channel 60 V, 4.8 mOhm logic level MOSFET in LPAK56 using Repetitive Avalanche technology

11 October 2024

Product data sheet

1. General description

Logic level N-channel MOSFET in an LPAK56 (Power SO8) package using Application Specific (ASFET) repetitive avalanche silicon technology. This product has been designed and qualified to AEC-Q101 for use in repetitive avalanche applications.

2. Features and benefits

- Fully automotive qualified to AEC-Q101 at 175 °C
- Repetitive Avalanche rated to 30 °C T_j rise:
 - Tested to 1 Bn avalanche events
- LPAK copper clip package technology:
 - High robustness and reliability
 - Gull wing leads for high manufacturability and AOI

3. Applications

- 12 V, 24 V and 48 V automotive systems
- Repetitive avalanche topologies
- Engine control
- Transmission control
- Actuator and auxiliary loads

4. Quick reference data

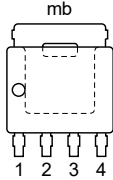
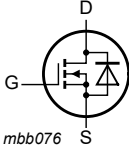
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$		-	-	60	V
I_D	drain current	$V_{GS} = 5\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 2	[1]	-	-	100	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 1		-	-	238	W
Static characteristics							
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 5\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; Fig. 14		-	3.3	4.8	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	$I_D = 25\text{ A}$; $V_{DS} = 48\text{ V}$; $V_{GS} = 5\text{ V}$; $T_j = 25\text{ °C}$; Fig. 16 ; Fig. 17		-	18.1	-	nC
Source-drain diode							
Q_r	recovered charge	$I_S = 20\text{ A}$; $dI_S/dt = -100\text{ A/μs}$; $V_{GS} = 0\text{ V}$; $V_{DS} = 25\text{ V}$; $T_j = 25\text{ °C}$		-	28	-	nC

[1] Continuous current is limited by package.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 LPAK56; Power-SO8 (SOT669)	 <i>mbb076</i>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9Y4R8-60RA	LPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9Y4R8-60RA	94RA860

8. Limiting values

Table 5. Limiting values

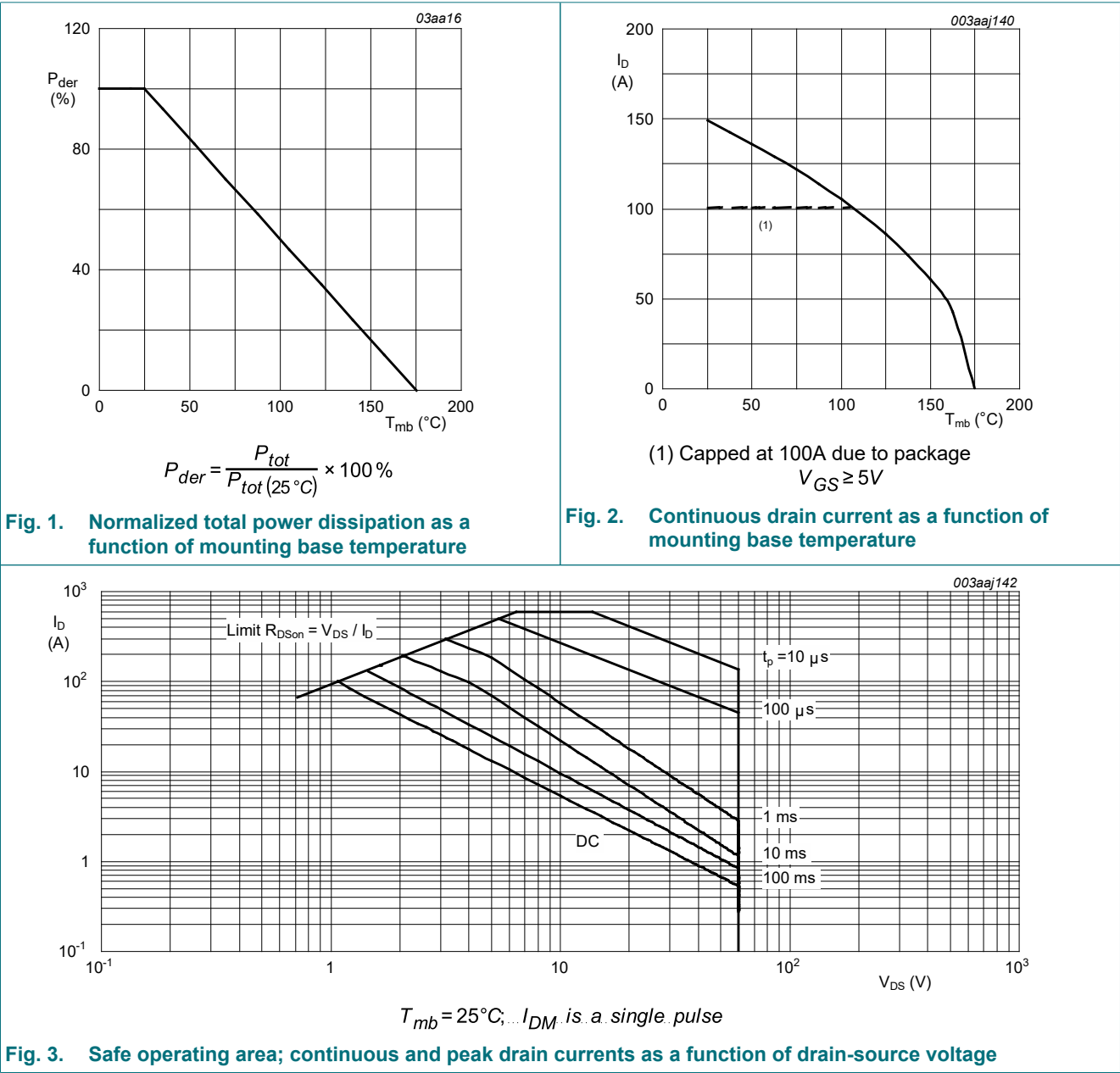
In accordance with the Absolute Maximum Rating System (IEC 60134). *T*_j = 25 °C unless otherwise stated.

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ <i>T</i> _j ≤ 175 °C		-	60	V
V _{DGR}	drain-gate voltage	<i>R</i> _{GS} = 20 kΩ		-	60	V
V _{GS}	gate-source voltage			-16	16	V
P _{tot}	total power dissipation	<i>T</i> _{mb} = 25 °C; Fig. 1		-	238	W
<i>I</i> _D	drain current	V _{GS} = 5 V; <i>T</i> _{mb} = 25 °C; Fig. 2	[1]	-	100	A
		V _{GS} = 5 V; <i>T</i> _{mb} = 100 °C; Fig. 2	[1]	-	100	A
<i>I</i> _{DM}	peak drain current	pulsed; <i>t</i> _p ≤ 10 μs; <i>T</i> _{mb} = 25 °C; Fig. 3		-	593	A
<i>T</i> _{stg}	storage temperature			-55	175	°C
<i>T</i> _j	junction temperature			-55	175	°C
Source-drain diode						
<i>I</i> _S	source current	<i>T</i> _{mb} = 25 °C	[1]	-	100	A
<i>I</i> _{SM}	peak source current	pulsed; <i>t</i> _p ≤ 10 μs; <i>T</i> _{mb} = 25 °C		-	593	A

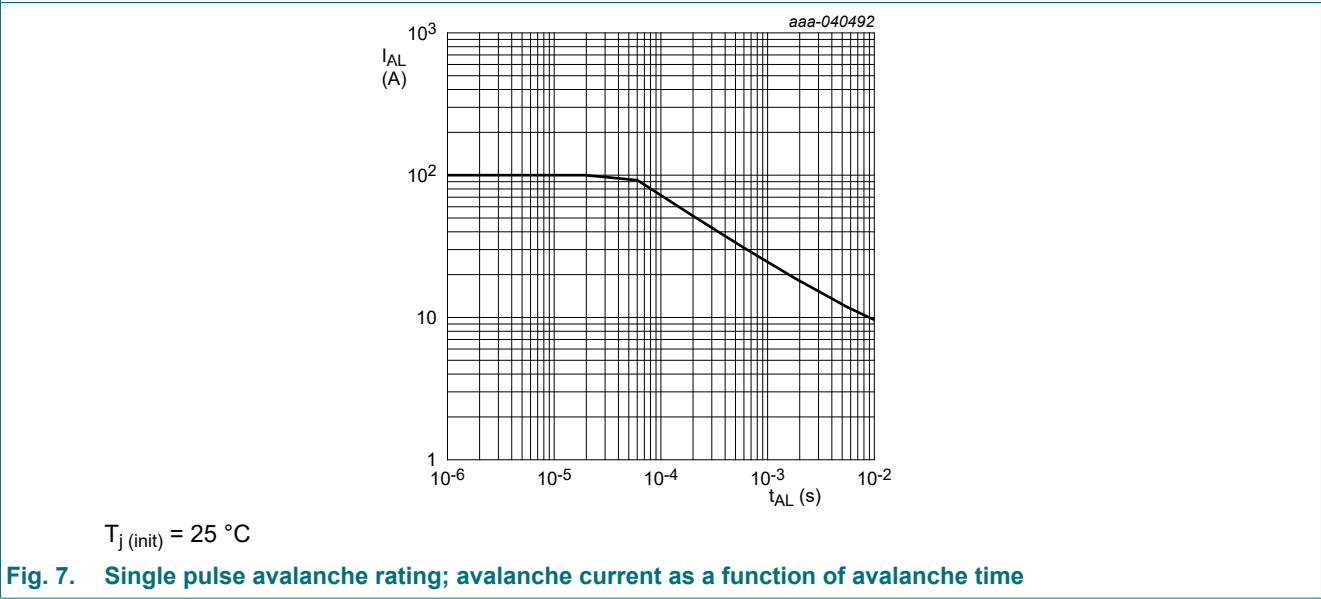
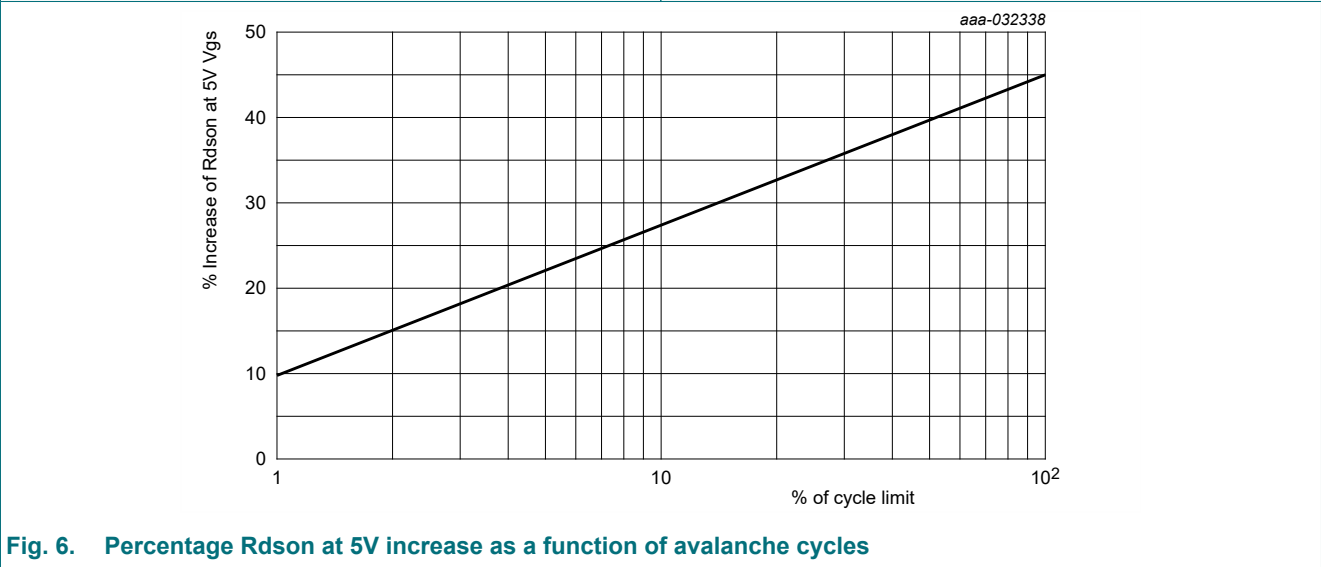
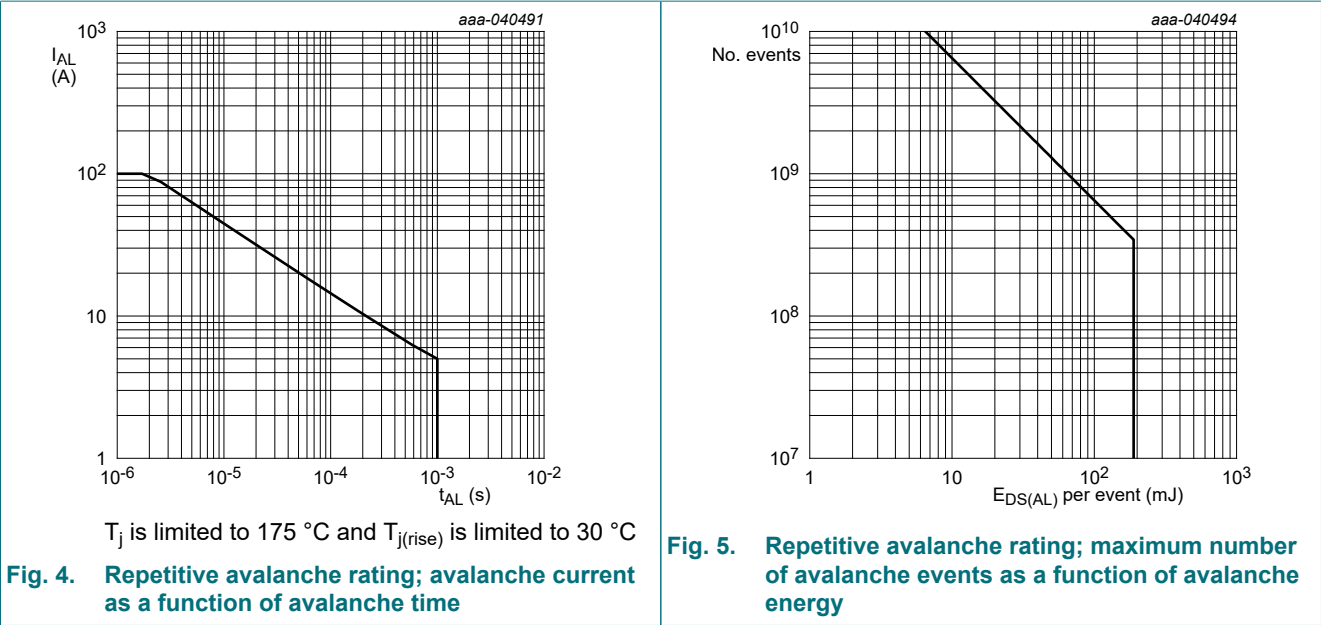
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Symbol	Parameter	Conditions		Min	Max	Unit
Avalanche ruggedness						
$E_{DS(AL)R}$	repetitive drain-source avalanche energy	$I_D = 4.9\text{ A}$; $V_{sup} \leq 60\text{ V}$; $R_{GS} = 10\ \Omega$; $V_{GS} = 10\text{ V}$; $T_{j(rise)} \leq 30\text{ }^\circ\text{C}$; unclamped; Fig. 4; Fig. 5; Fig. 6	[2] [3] [4]	-	189	mJ
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 100\text{ A}$; $V_{sup} \leq 60\text{ V}$; $R_{GS} = 50\ \Omega$; $V_{GS} = 5\text{ V}$; $T_{j(init)} = 25\text{ }^\circ\text{C}$; unclamped; Fig. 7	[5] [6]	-	199	mJ

- [1] Continuous current is limited by package.
- [2] Repetitive avalanche rating is limited by maximum junction temperature of 175 °C and junction rise of 30 °C
- [3] Refer to Fig. 5 for the limiting number of avalanche events
- [4] Refer to Fig. 6 R_{ds} at V_{gs}=5V will increase as a function of repetitive avalanche cycles
- [5] Refer to application note AN10273 for further information
- [6] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C



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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 8		-	-	0.63	K/W

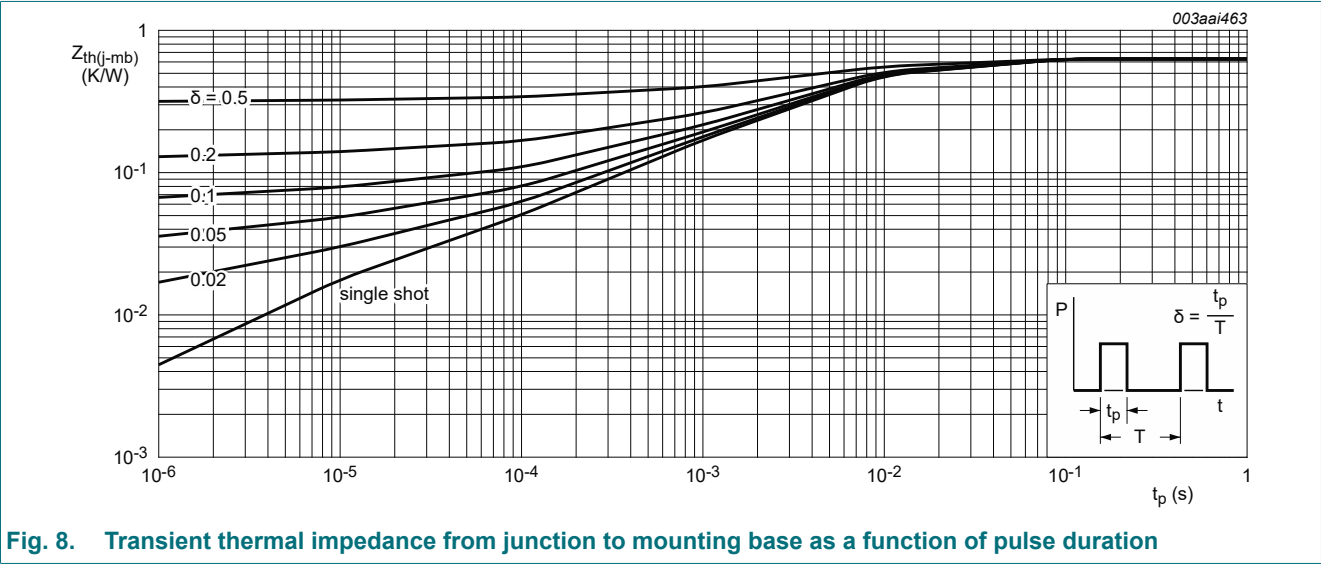


Fig. 8. Transient thermal impedance from junction to mounting base as a function of pulse duration

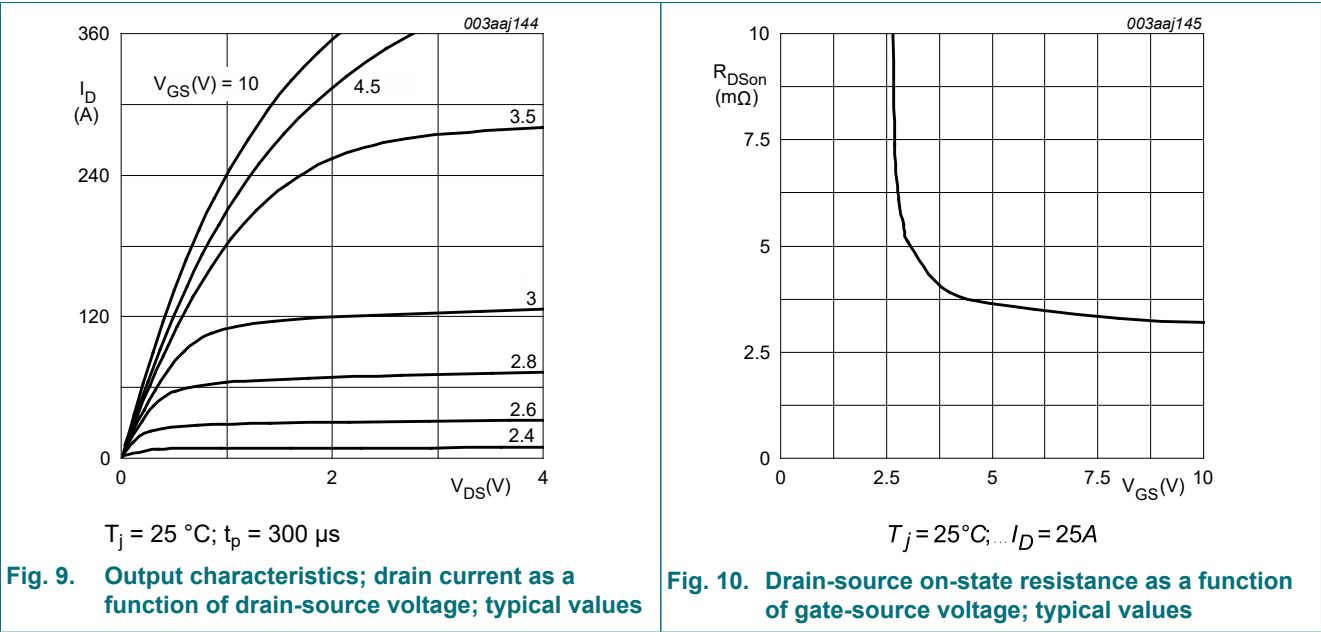
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\text{ }\mu\text{A}$; $V_{GS} = 0\text{ V}$; $T_J = 25\text{ }^\circ\text{C}$		60	-	-	V
		$I_D = 250\text{ }\mu\text{A}$; $V_{GS} = 0\text{ V}$; $T_J = -55\text{ }^\circ\text{C}$		54	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\text{ mA}$; $V_{DS}=V_{GS}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 12; Fig. 13		1.4	1.7	2.1	V
		$I_D = 1\text{ mA}$; $V_{DS}=V_{GS}$; $T_J = -55\text{ }^\circ\text{C}$; Fig. 12		-	-	2.45	V
		$I_D = 1\text{ mA}$; $V_{DS}=V_{GS}$; $T_J = 175\text{ }^\circ\text{C}$; Fig. 12		0.5	-	-	V
I_{DSS}	drain leakage current	$V_{DS} = 60\text{ V}$; $V_{GS} = 0\text{ V}$; $T_J = 25\text{ }^\circ\text{C}$		-	0.12	10	μA
		$V_{DS} = 60\text{ V}$; $V_{GS} = 0\text{ V}$; $T_J = 175\text{ }^\circ\text{C}$		-	-	500	μA
I_{GSS}	gate leakage current	$V_{GS} = 10\text{ V}$; $V_{DS} = 0\text{ V}$; $T_J = 25\text{ }^\circ\text{C}$		-	2	100	nA
		$V_{GS} = -10\text{ V}$; $V_{DS} = 0\text{ V}$; $T_J = 25\text{ }^\circ\text{C}$		-	2	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 5\text{ V}$; $I_D = 25\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 14		-	3.3	4.8	m Ω
		$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 14		-	2.9	4.1	m Ω
		$V_{GS} = 5\text{ V}$; $I_D = 25\text{ A}$; $T_J = 175\text{ }^\circ\text{C}$; Fig. 14; Fig. 15		-	-	10.8	m Ω

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Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Dynamic characteristics							
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 48 V; V _{GS} = 5 V; T _j = 25 °C; Fig. 16 ; Fig. 17		-	54.8	-	nC
Q _{GS}	gate-source charge			-	13.6	-	nC
Q _{GD}	gate-drain charge			-	18.1	-	nC
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz; T _j = 25 °C; Fig. 18		-	5890	7853	pF
C _{Oss}	output capacitance			-	506	607	pF
C _{rss}	reverse transfer capacitance			-	276	378	pF
t _{d(on)}	turn-on delay time	V _{DS} = 45 V; R _L = 1.8 Ω; V _{GS} = 5 V; R _{G(ext)} = 5 Ω; T _j = 25 °C		-	28	-	ns
t _r	rise time			-	53	-	ns
t _{d(off)}	turn-off delay time			-	80	-	ns
t _f	fall time			-	47	-	ns
Source-drain diode							
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; Fig. 19		-	0.78	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V;		-	29	-	ns
Q _r	recovered charge	V _{DS} = 25 V; T _j = 25 °C		-	28	-	nC



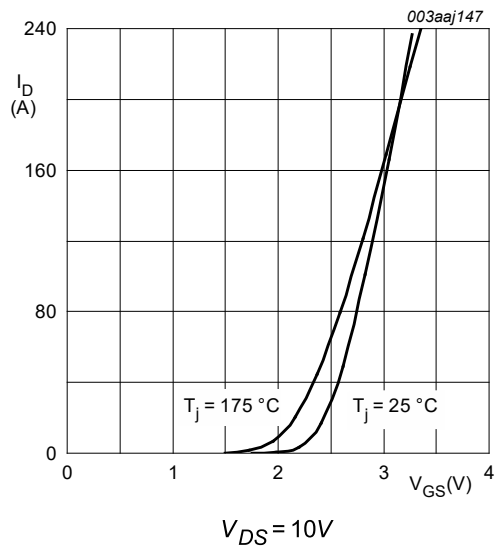


Fig. 11. Transfer characteristics; drain current as a function of gate-source voltage; typical values

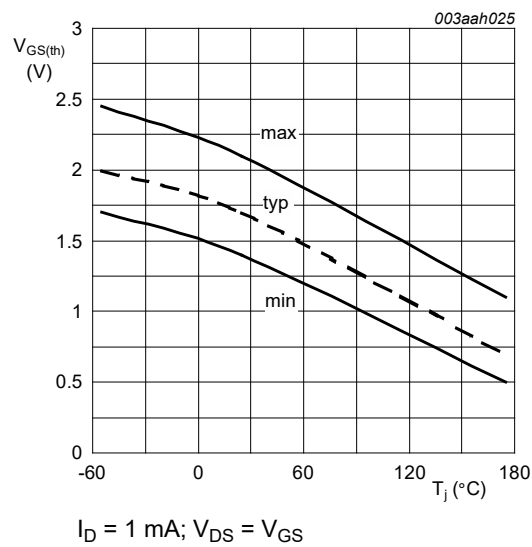


Fig. 12. Gate-source threshold voltage as a function of junction temperature

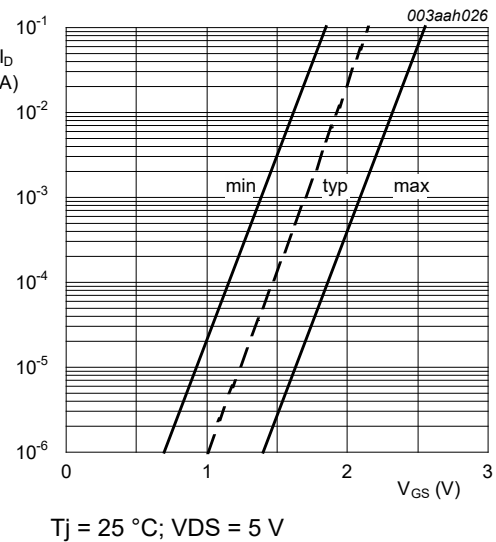


Fig. 13. Sub-threshold drain current as a function of gate-source voltage

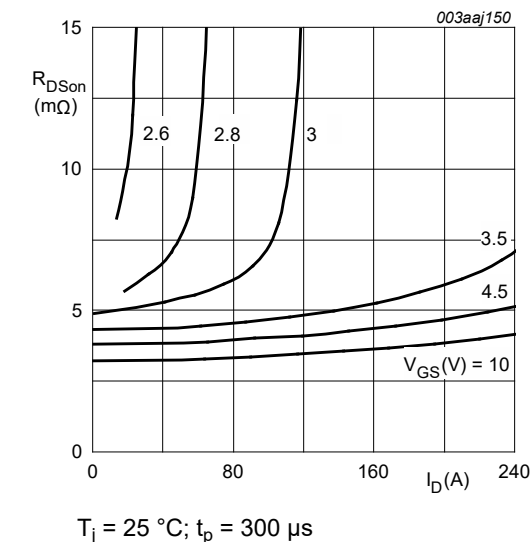


Fig. 14. Drain-source on-state resistance as a function of drain current; typical values

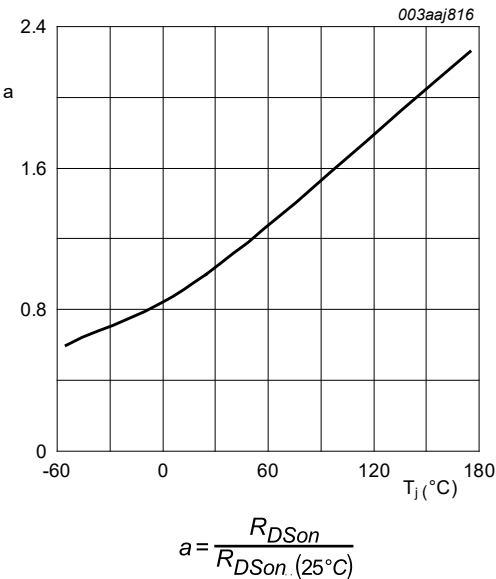


Fig. 15. Normalized drain-source on-state resistance factor as a function of junction temperature

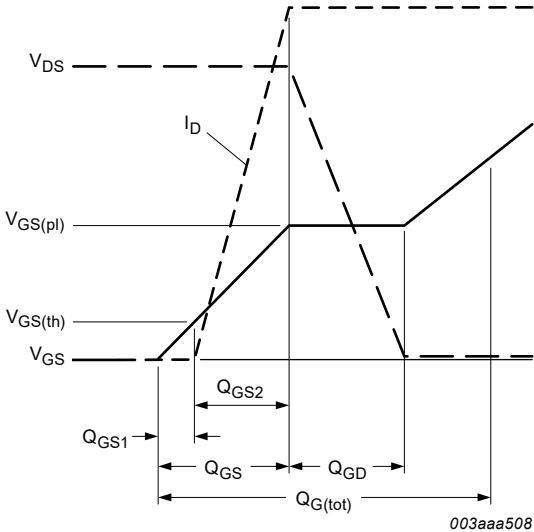


Fig. 16. Gate charge waveform definitions

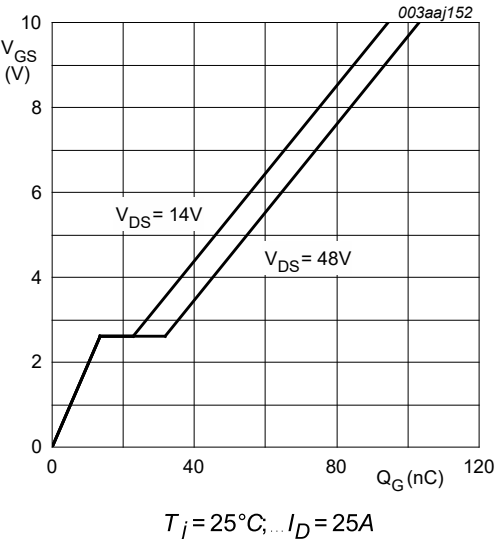


Fig. 17. Gate-source voltage as a function of gate charge; typical values

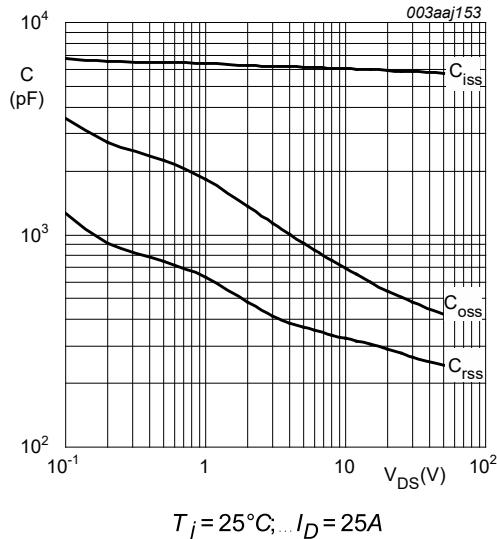


Fig. 18. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

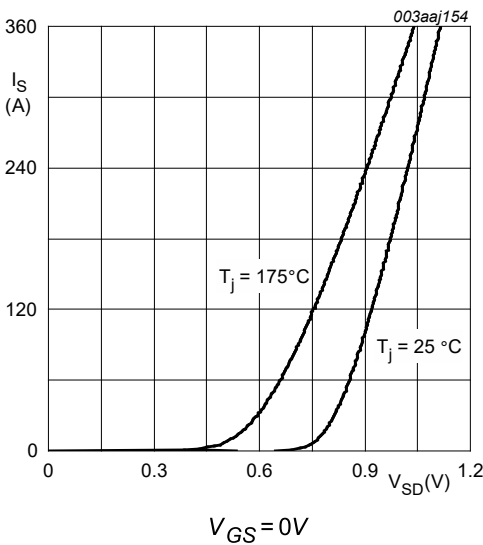


Fig. 19. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

11. Package outline

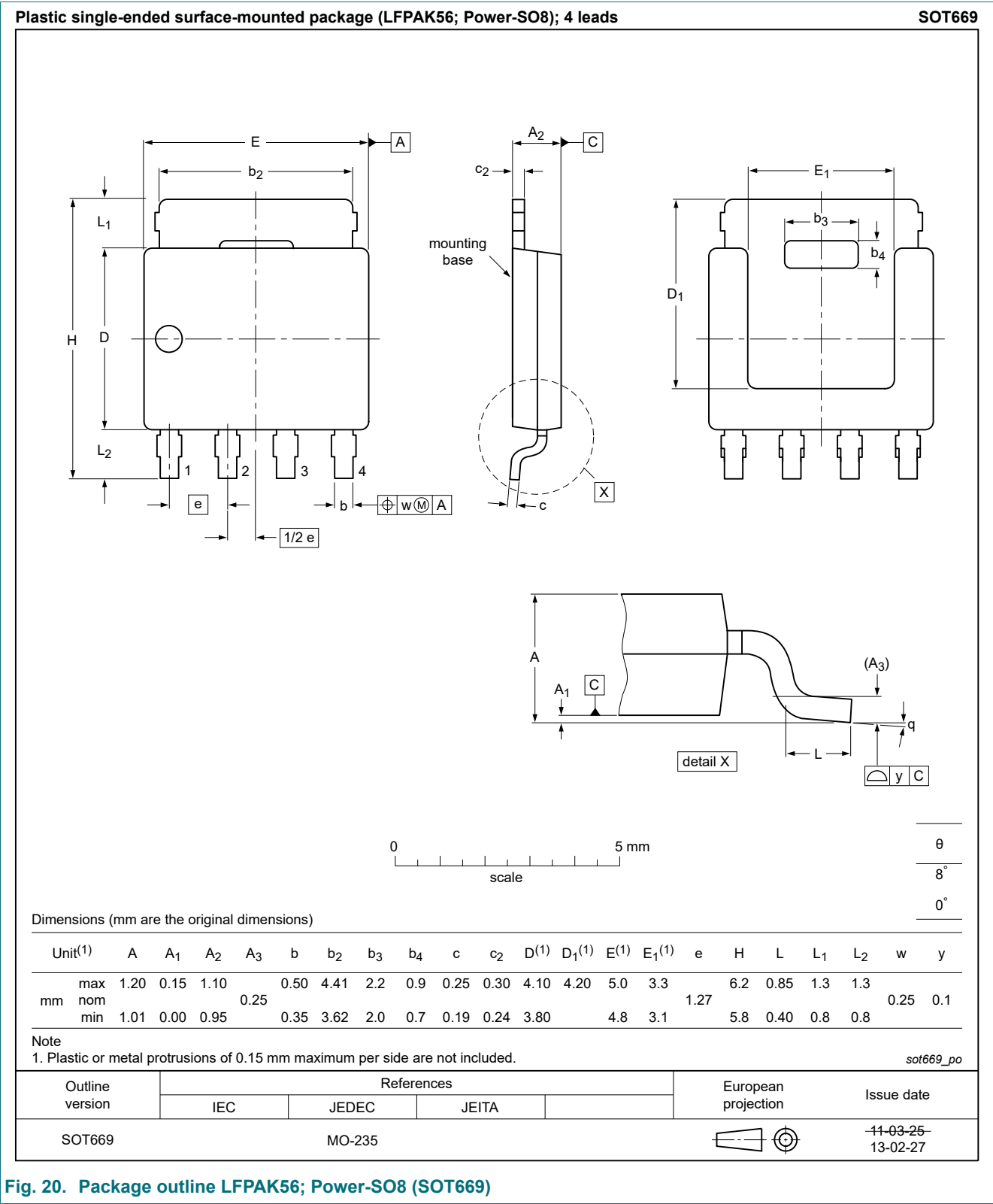


Fig. 20. Package outline LPAK56; Power-SO8 (SOT669)

12. Soldering

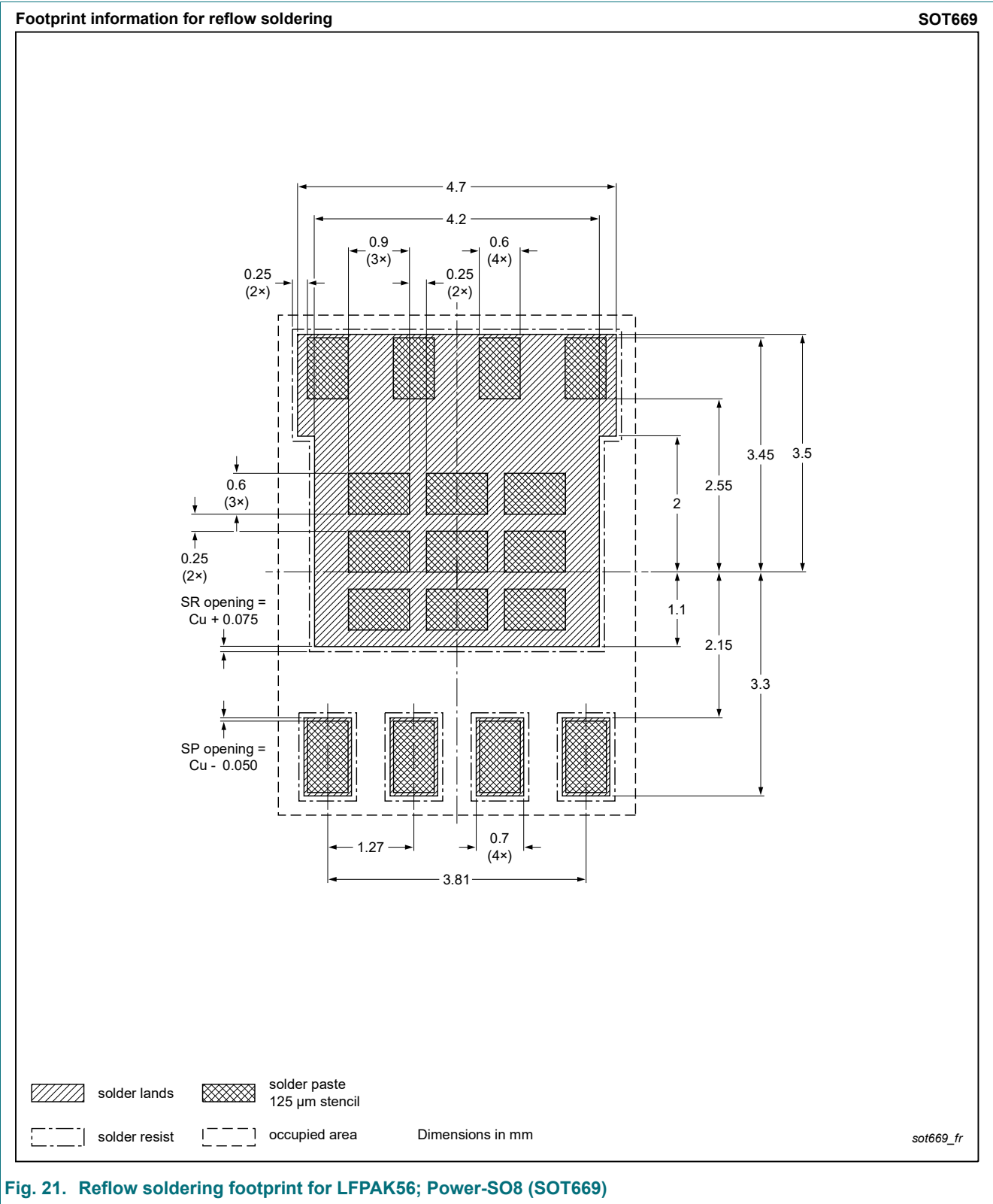


Fig. 21. Reflow soldering footprint for LPAK56; Power-SO8 (SOT669)

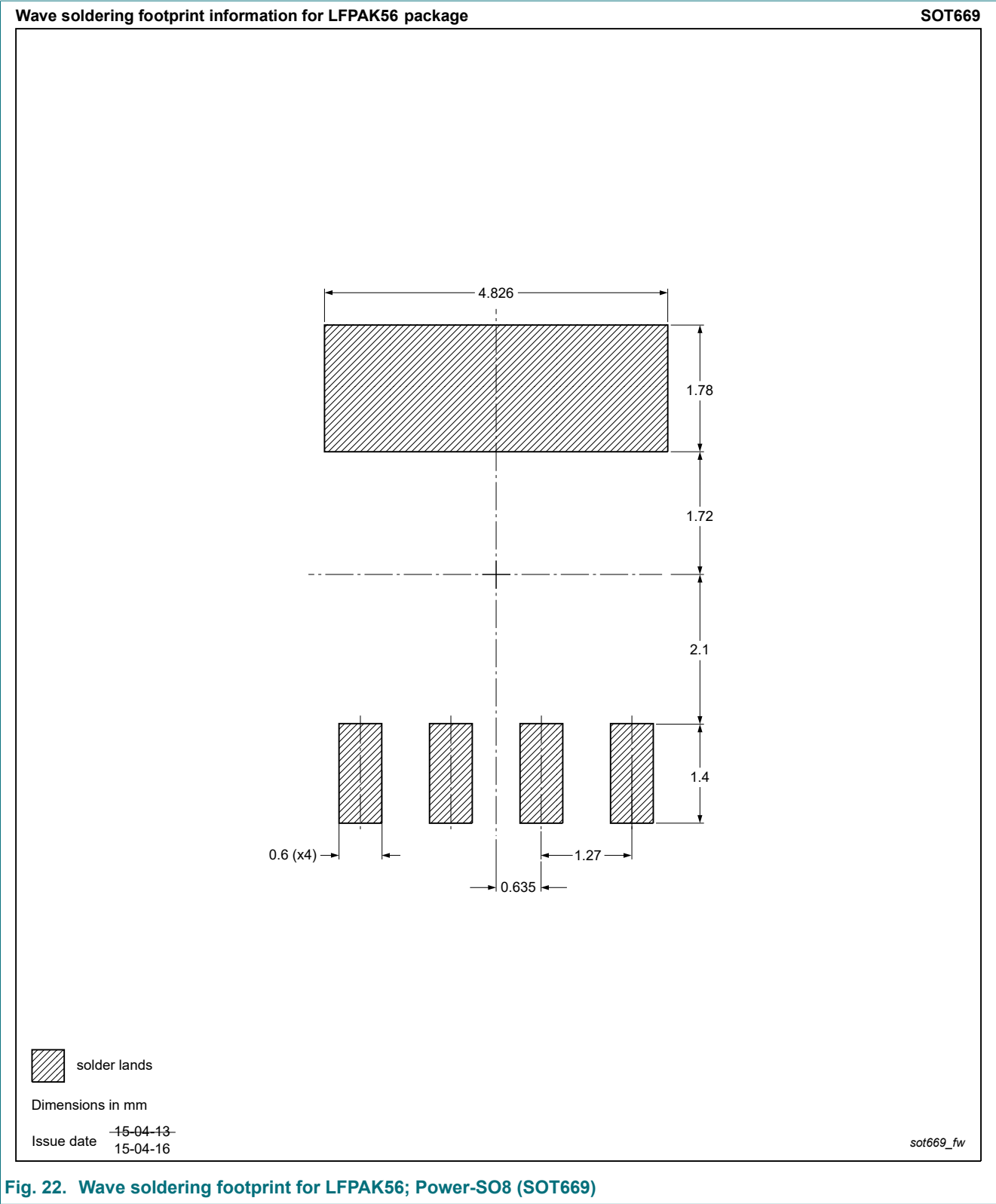


Fig. 22. Wave soldering footprint for LPAK56; Power-SO8 (SOT669)

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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